

Title (en)

Surface treatment method and surface treatment apparatus

Title (de)

Verfahren zur Oberflächenbehandlung und Vorrichtung zur Oberflächenbehandlung

Title (fr)

Procédé et appareil de traitement de surface

Publication

EP 1981073 A3 20111026 (EN)

Application

EP 08161430 A 19991111

Priority

- EP 99122000 A 19991111
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Abstract (en)

[origin: EP1001454A2] A subject (W) which is to be treated and on which an oxide film is formed, is carried into a treatment vessel (10), and the treatment vessel is maintained under vacuum. A mixture gas of N₂ gas and H₂ gas is introduced into a plasma generation section (30), plasma is generated, and activated gas species of the N₂ and H₂ gases are formed. The activated gas species are caused to flow toward the subject, and an NF₃ gas is added to the activated gas species and activated to generate an activated gas of N₂, H₂ and NF₃ gases. The subject (W) is cooled to not higher than a predetermined temperature by a cooling means and reacted with the activated gas of NF₃ gas. The oxide film is thus degenerated into a reactive film. When the supply of N₂, H₂ and NF₃ gases into the treatment vessel (10) is stopped, the subject is heated up to a predetermined temperature by a heating means, and the reactive film is sublimated and eliminated. Thus, a surface treatment method for removing the oxide film from the subject and a surface treatment apparatus for doing the same are disclosed. Furthermore, the surface treatment apparatus and other treatment apparatuses constitute a cluster system capable of carrying the subject in an unreactive atmosphere. <IMAGE>

IPC 8 full level

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Citation (search report)

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